

Excellent Integrated System Limited

Stocking Distributor

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Vishay/Siliconix SI7882DP-T1-GE3

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Si7882DP

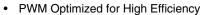
Vishay Siliconix

N-Channel Reduced Q_g, Fast Switching MOSFET

| PRODUCT SUMMARY | | | | |
|---------------------|--------------------------------------|--------------------|--|--|
| V _{DS} (V) | $R_{DS(on)}\left(\Omega\right)$ | I _D (A) | | |
| 12 | 0.0055 at $V_{GS} = 4.5 \text{ V}$ | 22 | | |
| | 0.008 at V _{GS} = 2.5 V | 18 | | |

FEATURES

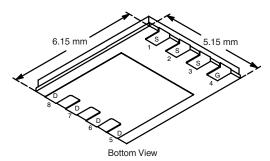
- · Halogen-free available
- TrenchFET[®] Power MOSFET
- New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile



100 % R_a Tested



PowerPAK SO-8



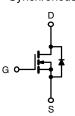
Ordering Information: Si7882DP-T1

Si7882DP-T1-E3 (Lead (Pb)-free)

Si7882DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

- · Point-of-Load Synchronous Rectifier
 - 5 V or 3.3 V BUS Step Down
 - Q_q Optimized for 500 kHz Operation
- Synchronous Buck, Shoot-Thru Resistant



N-Channel MOSFET

| Parameter | | Symbol | 10 s | Steady State | Unit |
|--|------------------------|-----------------------------------|-------------|--------------|------|
| Drain-Source Voltage | | V_{DS} | 12 | | V |
| Gate-Source Voltage | | V_{GS} | ± 8 | | |
| Continuous Drain Current (T _{.I} = 150 °C) ^a | T _A = 25 °C | l _a | 22 | 13 | |
| Continuous Drain Current (1,j = 150 °C) | T _A = 70 °C | - I _D | 18 | 11 | |
| Pulsed Drain Current | | I _{DM} | 50 | | Α |
| Continuous Source Current (Diode Conduction) ^a | | I _S | 4.1 | 1.6 | |
| Single Pulse Avalanche Energy | L = 0.1 mH | I _{AS} | 12 7.2 | | |
| Avalanche Energy | L = 0.1 IIII1 | E _{AS} | | | mJ |
| Maniana Barra Birainatian d | T _A = 25 °C | P _D | 5 | 1.9 | W |
| Maximum Power Dissipation ^a | T _A = 70 °C | | 3.2 | 1.2 | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | | °C |
| Soldering Recommendations (Peak Temperature | , | 260 | | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|---|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| Maximum lunction to Ambient (MOCFET) | t ≤ 10 s | R _{thJA} | 20 | 25 | °C/W | |
| Maximum Junction-to-Ambient (MOSFET) ^a | Steady State | | 55 | 65 | | |
| Maximum Junction-to-Case (Drain) | Steady State | R _{thJC} | 2.0 | 2.6 | | |

Notes

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

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Datasheet of SI7882DP-T1-GE3 - MOSFET N-CH 12V 13A PPAK SO-8

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Si7882DP

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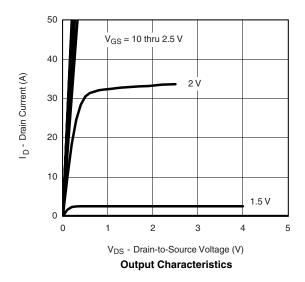
| SPECIFICATIONS T _J = 25 °C, unless otherwise noted | | | | | | | | |
|--|---------------------|---|------|--------|--------|------|--|--|
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | | |
| Static | | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_D = 250 \mu A$ | 0.6 | | 1.4 | ٧ | | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$ | | | ± 100 | nA | | |
| Zara Cata Valtaga Drain Current | 1 | V _{DS} = 12 V, V _{GS} = 0 V | 1 | | 1 | | | |
| Zero Gate Voltage Drain Current | IDSS | V _{DS} = 12 V, V _{GS} = 0 V, T _J = 70 °C | | | 5 | μΑ | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$ | 40 | | | Α | | |
| D : 0 | В | $V_{GS} = 4.5 \text{ V}, I_D = 17 \text{ A}$ | | 0.0045 | 0.0055 | Ω | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | $V_{GS} = 2.5 \text{ V}, I_D = 14 \text{ A}$ | | 0.0065 | 0.008 | | | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = 6 V, I _D = 17 A | | 80 | | S | | |
| Diode Forward Voltage ^a | V_{SD} | I _S = 2.7 A, V _{GS} = 0 V | | 0.70 | 1.1 | V | | |
| Dynamic ^b | | | | | | | | |
| Total Gate Charge | Q_g | | | 21 | 30 | | | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = 6 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 17 \text{ A}$ | | 4.6 | | nC | | |
| Gate-Drain Charge | Q_{gd} | | | 3.5 | | İ | | |
| Gate Resistance | R_g | | 0.8 | | 3.5 | Ω | | |
| Turn-On Delay Time | t _{d(on)} | | | 28 | 42 | | | |
| Rise Time | t _r | V_{DD} = 6 V, R_L = 6 Ω | | 32 | 48 | | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω | | 82 | 123 | ns | | |
| Fall Time t _f | | | | 35 | 53 | | | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = 2.7 A, di/dt = 100 A/μs | | 60 | 90 | | | |

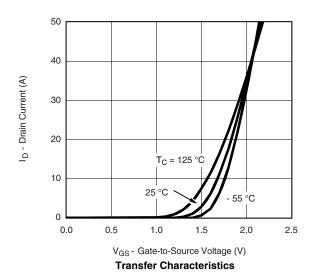
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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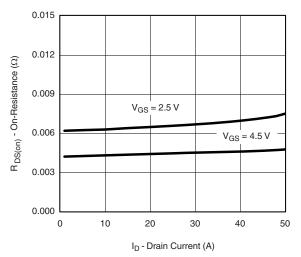
V_{GS} - Gate-to-Source Voltage (V)

Is - Source Current (A)

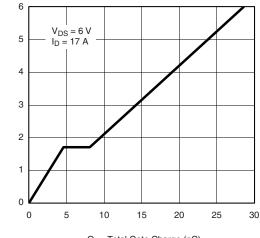
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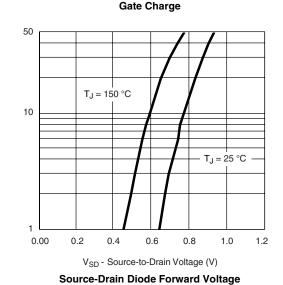
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current



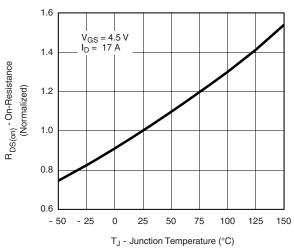
Q_g - Total Gate Charge (nC)



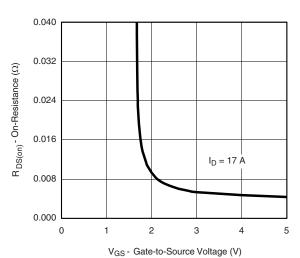
4000 3200 C_{iss} C_{oss} C_{oss} 0 0 2 4 6 8 10 12

 V_{DS} - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

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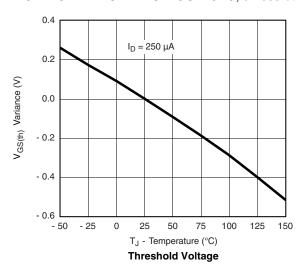


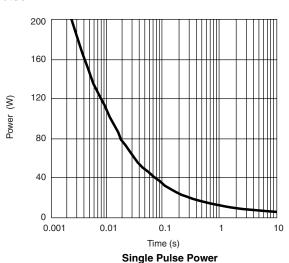
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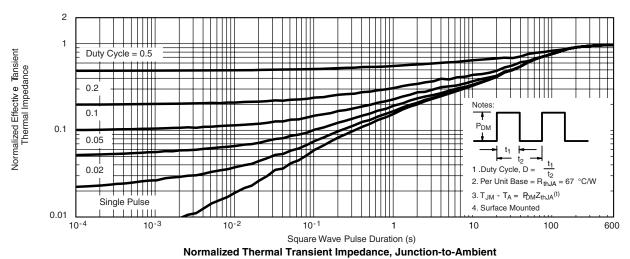
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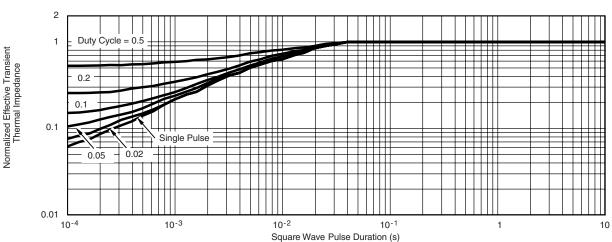
VISHAY.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted









Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?71858.



Distributor of Vishay/Siliconix: Excellent Integrated System Limited

Datasheet of SI7882DP-T1-GE3 - MOSFET N-CH 12V 13A PPAK SO-8

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